

ABSTRACT

A method for fabrication of ferroelectric capacitor elements of an integrated circuit includes steps of deposition of an electrically conductive bottom electrode layer, preferably made of a noble metal. The bottom electrode is covered with a layer of ferroelectric dielectric material. The ferroelectric dielectric is annealed with a first anneal prior to depositing a second electrode layer comprising a noble metal oxide. Deposition of the electrically conductive top electrode layer is followed by annealing the layer of ferroelectric dielectric material and the top electrode layer with a second anneal. The first and the second anneal are performed by rapid thermal annealing.